

MMBFJ177LT1G, SMMBFJ177LT1G

JFET Chopper

P-Channel – Depletion

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain–Gate Voltage	V_{DG}	-25	Vdc
Gate–Source Voltage	V_{GS}	25	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

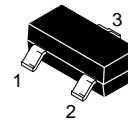
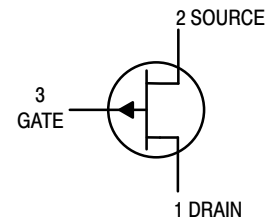
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.



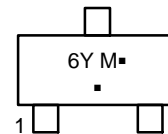
ON Semiconductor®

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SOT-23 (TO-236AB)
CASE 318-08
STYLE 10

MARKING DIAGRAM



6Y = Specific Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBFJ177LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SMMBFJ177LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Gate-Source Breakdown Voltage (V _{DS} = 0, I _D = 1.0 μAdc)	V _{(BR)GSS}	30	-	Vdc
Gate Reverse Current (V _{DS} = 0 Vdc, V _{GS} = 20 Vdc)	I _{GSS}	-	1.0	nAdc
Gate Source Cutoff Voltage (V _{DS} = -15 Vdc, I _D = -10 nAdc)	V _{GS(off)}	0.8	2.5	Vdc

ON CHARACTERISTICS

Zero-Gate-Voltage Drain Current (V _{GS} = 0, V _{DS} = -15 Vdc) (Note 2)	I _{DSS}	-1.5	-20	mAdc	
Drain Cutoff Current (V _{DS} = -15 Vdc, V _{GS} = 10 Vdc)	I _{D(off)}	-	-1.0	nAdc	
Drain Source On Resistance (I _D = -500 μAdc)	r _{DS(on)}	-	300	Ω	
Input Capacitance	V _{DS} = 0, V _{GS} = 10 Vdc f = 1.0 MHz	C _{iss}	-	11	pF
Reverse Transfer Capacitance		C _{rss}	-	5.5	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width < 300 μs, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

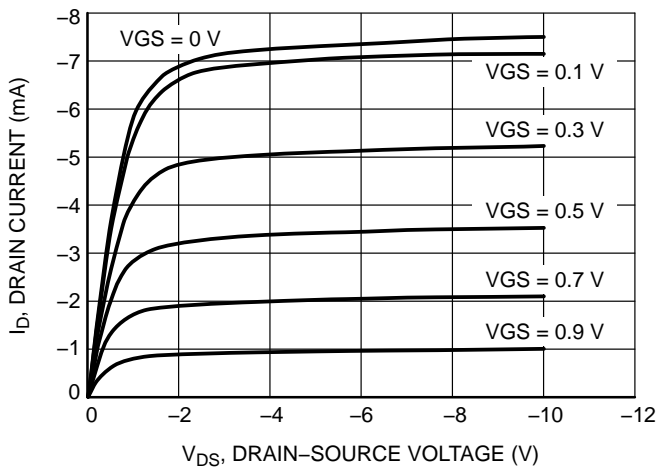


Figure 1. Drain Current vs. Drain-Source Voltage

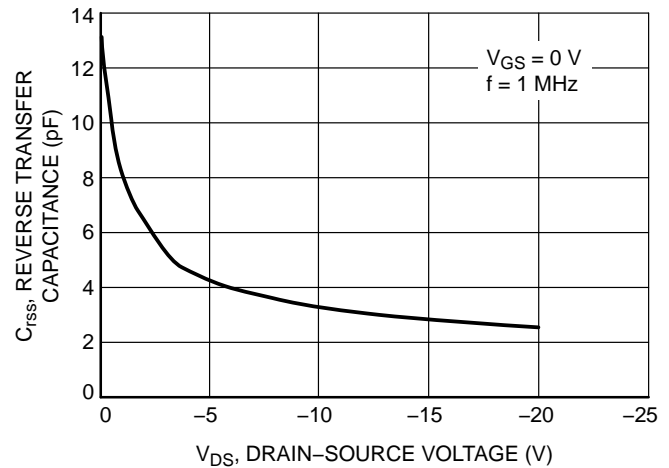


Figure 2. Reverse Transfer Capacitance

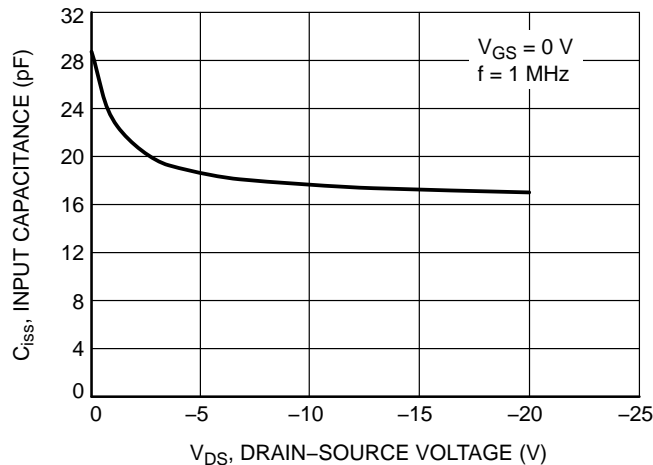
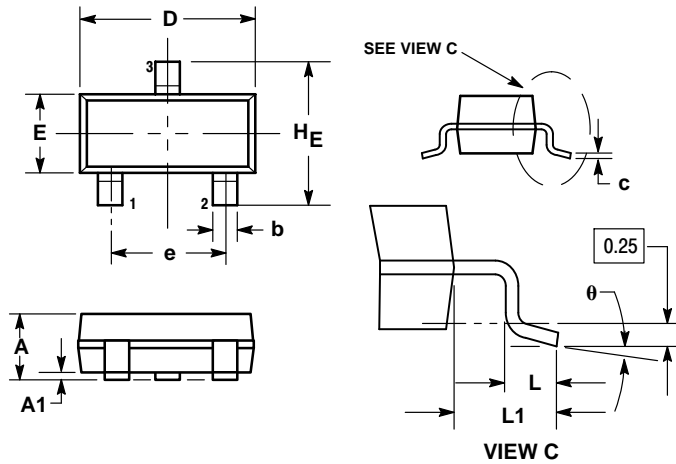


Figure 3. Input Capacitance

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PACKAGE DIMENSIONS

SOT-23 (TO-236AB) CASE 318-08 ISSUE AP

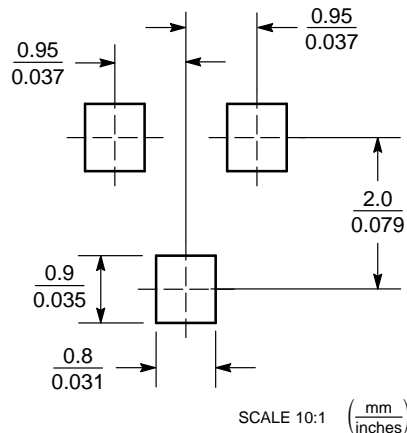


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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